

ABSTRACT OF THE DISCLOSURE

1 Since each wiring line is formed on one surface of the
2 associated beam at a prescribed width over the entire length of
3 the beam, the beam has the same sectional shape taken in the
4 width direction at any point along an arbitrary longitudinal
5 direction of the beam. As a result, the second moment of area,
6 which is determined by the shapes of the beam and the wiring
7 line, is uniform. This prevents a problem of the curvature of a
8 beam varying locally when the beam is bent by a prescribed amount
9 due to contact of the probe with a pad of a subject body. This,
10 in turn, prevents local concentration of stress in the beams and
11 thereby prevents breakage of the beam. Therefore, the probe
12 structure can be miniaturized while the strength of the beams is
13 kept at a required level, whereby a semiconductor device testing
14 apparatus capable of accommodating many probes can be realized.